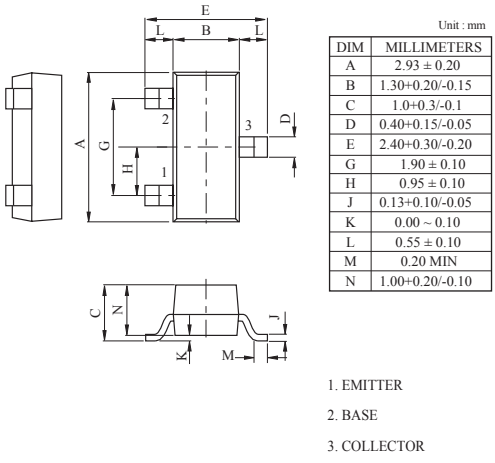
MMBTA56

EPITAXIAL PLANAR PNP TRANSISTOR

AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

FEATURE

- Complementary to MMBTA06
- Suffix **U** : Qualified to AEC-Q101.
  ex) MMBTA56-RTK/H**U**



Unit : mm

DIM	MILLIMETERS
A	2.93 ± 0.20
B	1.30+0.20/-0.15
C	1.0+0.3/-0.1
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90 ± 0.10
H	0.95 ± 0.10
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55 ± 0.10
M	0.20 MIN
N	1.00+0.20/-0.10

1. EMITTER
2. BASE
3. COLLECTOR

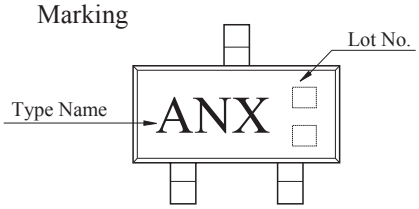
SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Emitter Current	I_E	500	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 ~ 150	℃

* : Package Mounted On 99.5% Alumina 10 × 8 × 0.6mm.

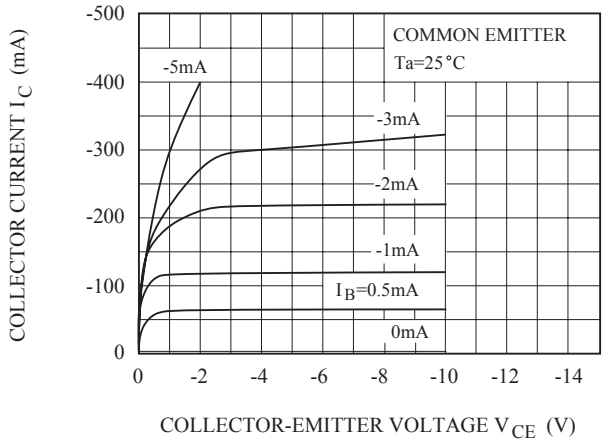
Marking



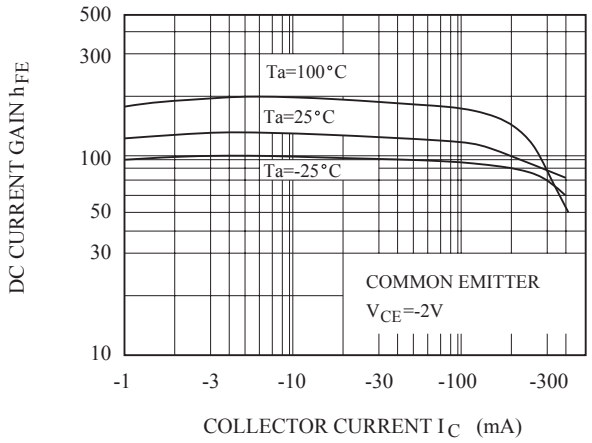
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-80V, $I_{E=0}$	-	-	-100	nA
Emitter Cut-off Current	I_{CEO}	V_{CE}=-60V, I_B=0	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-80	-	-	V
DC Current Gain	$h_{FE}(1)$	V_{CE}=-1V, I_C=-10mA	100	-	-	
	$h_{FE}(2)$	V_{CE}=-1V, I_C=-100mA	100	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-0.25	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-100mA	-	-	-1.2	V
Transition Frequency	f_T	V_{CE}=-1V, I_C=-100mA	50	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	14	-	pF

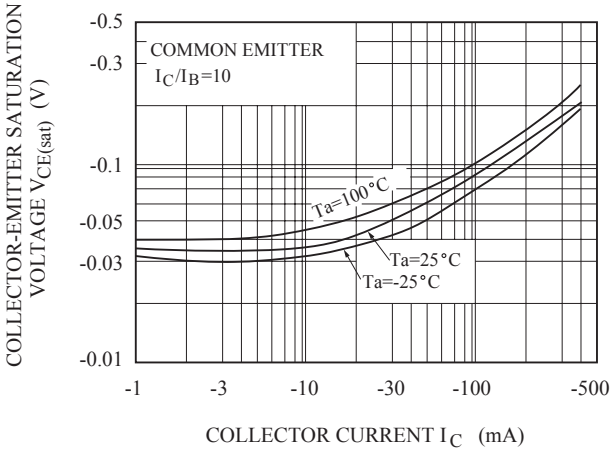
I_C - V_{CE}



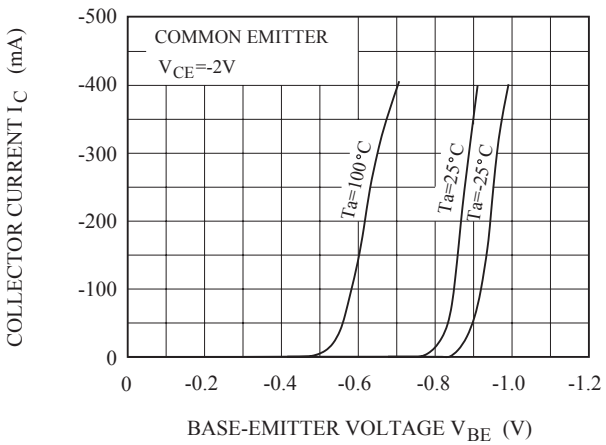
h_{FE} - I_C



$V_{CE(sat)}$ - I_C



I_C - V_{BE}



Pc - Ta